

MICROWAVE POWER GaAs FET

TIM1213-18L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 42.5dBm at 12.7GHz to 13.2GHz

·HIGH GAIN

G1dB= 6.0dB at 12.7GHz to 13.2GHz

·LOW INTERMODULATION DISTORTION

IM3= -28dBc at Pout= 36.0dBm

Single Carrier Level

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 4.4A f = 12.7 to 13.2GHz	dBm	42.0	42.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	5.0	6.0	
Drain Current	IDS1		Α	_	5.5	6.0
Gain Flatness	ΔG		dB		_	±0.8
Power Added Efficiency	ηadd		%		28	
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 36.0dBm, Δf = 5MHz (Single Carrier Level)	dBc	-25	-28	_
Drain Current	IDS2		Α	_	5.5	6.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 100 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	S	_	4.5	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-0.7	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	10.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -145 _μ A	٧	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.8	2.3

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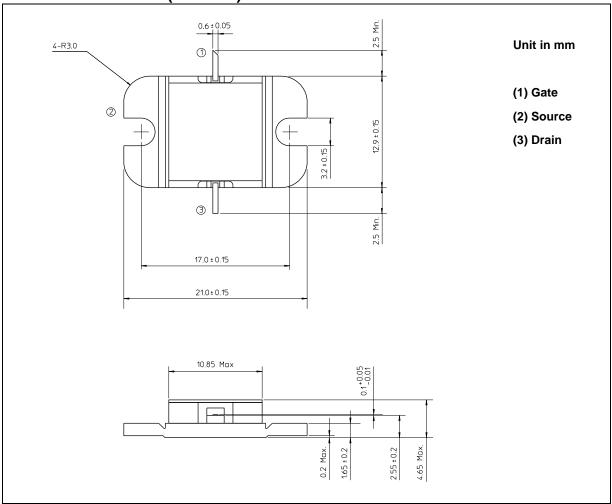
- MICROWAVE SEMICONDUCTOR TECHNICAL DATA



ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	11.5
Total Power Dissipation (Tc= 25°C)	PT	W	65
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11C1B)

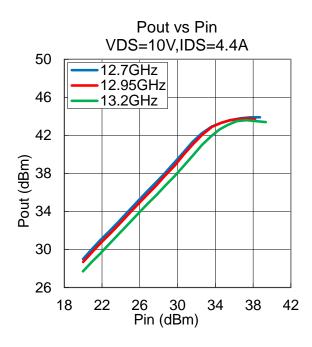


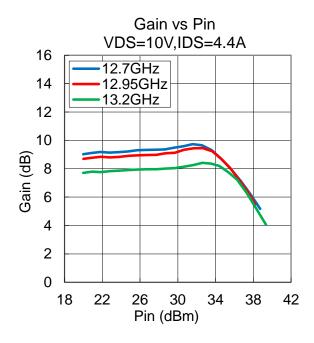
HANDLING PRECAUTIONS FOR PACKAGE MODEL

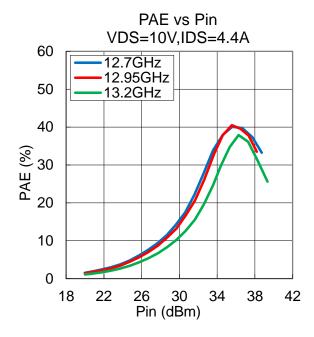
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

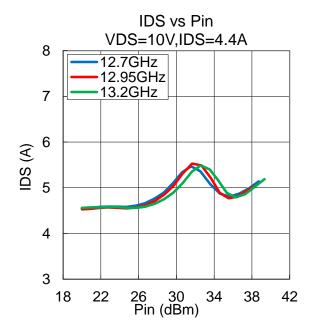
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 4.4 A, f= 12.7, 12.95, 13.2 GHz, Ta= +25 °C





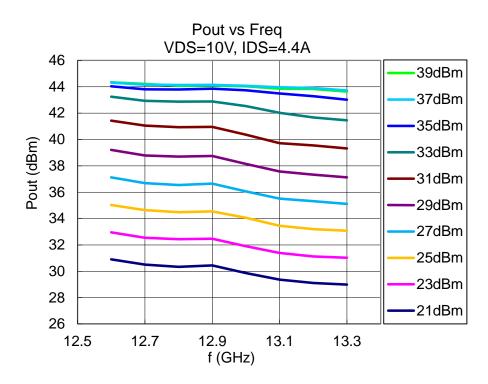






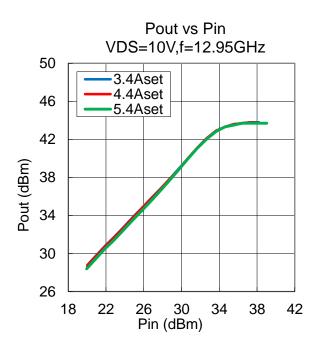
·Pout vs. Frequency

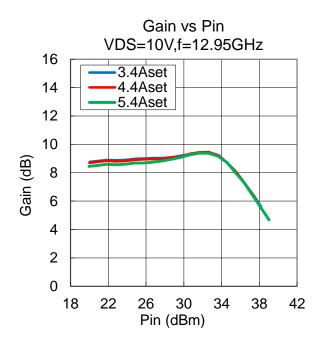
VDS= 10 V, IDSset= 4.4 A, Ta= +25 °C

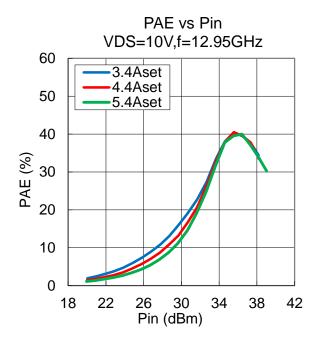


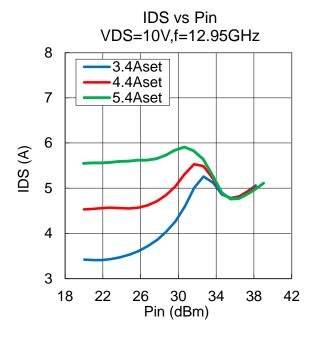
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 3.4, 4.4, 5.4 A, f= 12.95 GHz, Ta= +25 °C



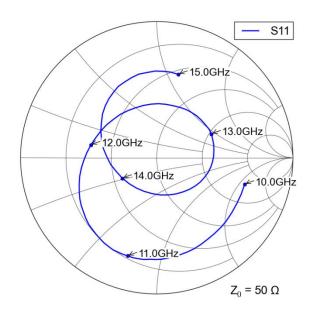


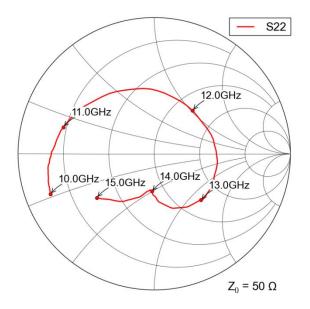


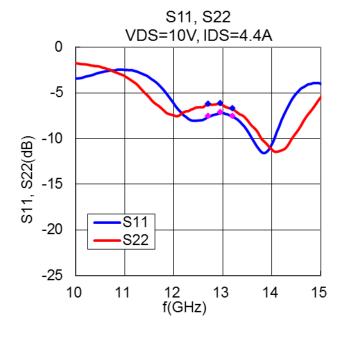


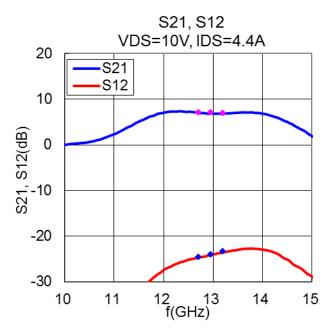
-S-Parameters

VDS= 10 V, IDSset= 4.4 A, f= 10.0 to 15.0 GHz, Ta= +25 °C











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